

General Description

The WST05P06 is the highest performance trench P-Ch MOSFET with extreme high cell density, which provide excellent $R_{DS(on)}$ and gate charge for most of the synchronous buck converter applications.

The WST05P06 meet the RoHS and Green Product requirement, with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

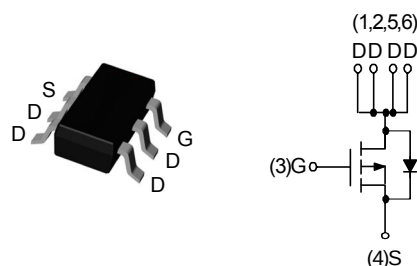
Product Summary

BVDSS	$R_{DS(on)}$	I_D
-60V	68m Ω	-4.9A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

SOT- 23-6L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-4.9	A
$I_D@T_C=70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-3.3	A
I_{DM}	Pulsed Drain Current ²	-11	A
$P_D@T_A=25^\circ C$	Total Power Dissipation ³	1.3	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	125	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	80	$^\circ C/W$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-60	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=-1\text{mA}$	---	-0.014	---	V/ $^{\circ}\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V$, $I_D=-4.9A$	---	68	85	$\text{m}\Omega$
		$V_{GS}=-4.5V$, $I_D=-2.5A$	---	80	110	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu A$	-0.5	-0.8	-1.2	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	3.95	---	mV/ $^{\circ}\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-48V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	-1	μA
		$V_{DS}=-48V$, $V_{GS}=0V$, $T_J=55^{\circ}\text{C}$	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-5V$, $I_D=-2.9A$	---	11	---	S
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-30V$, $V_{GS}=-4.5V$, $I_D=-2.9A$	---	11	15.4	nC
Q_{gs}	Gate-Source Charge		---	1.4	2.1	
Q_{gd}	Gate-Drain Charge		---	2.4	3.2	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-30V$, $V_{GS}=-4.5V$, $R_G=3.3\Omega$, $I_D=-2.9A$	---	8.5	16	ns
T_r	Rise Time		---	5.8	11	
$T_{d(off)}$	Turn-Off Delay Time		---	36	65	
T_f	Fall Time		---	5.6	11	
C_{iss}	Input Capacitance	$V_{DS}=-30V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	430	560	pF
C_{oss}	Output Capacitance		---	41	66	
C_{rss}	Reverse Transfer Capacitance		---	25	35	

Diode Characteristics

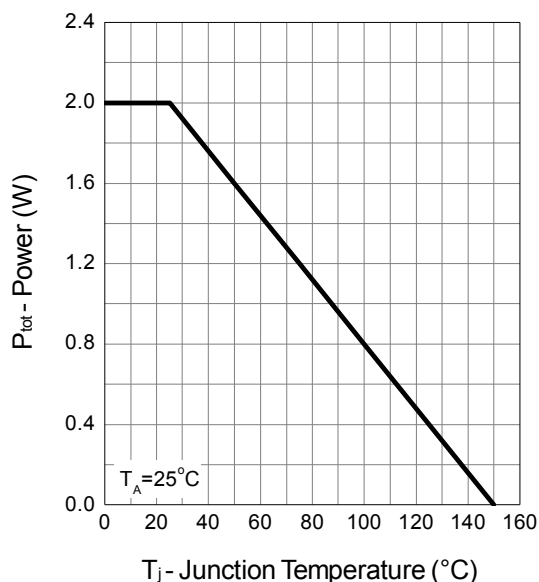
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	-4.9	A
I_{SM}	Pulsed Source Current ^{2,4}		---	---	-11	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=-1A$, $T_J=25^{\circ}\text{C}$	---	---	-1	V
t_{rr}	Reverse Recovery Time	$I_F=-2.9A$, $dI/dt=100A/\mu s$, $T_J=25^{\circ}\text{C}$	---	20	---	nS
Q_{rr}	Reverse Recovery Charge		---	19	---	nC

Note :

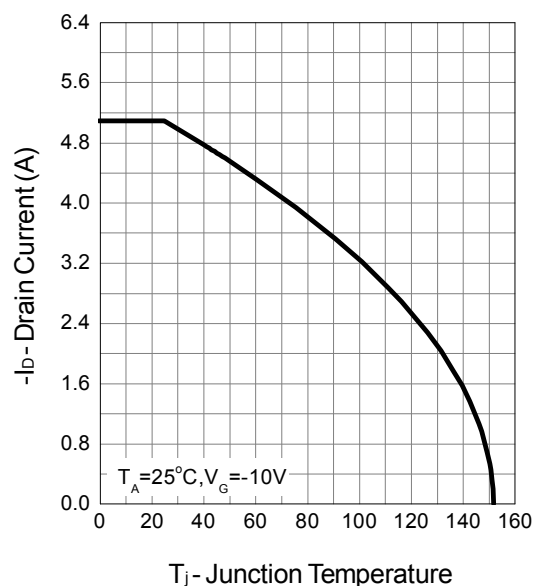
- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper, $t < 10\text{sec}$.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

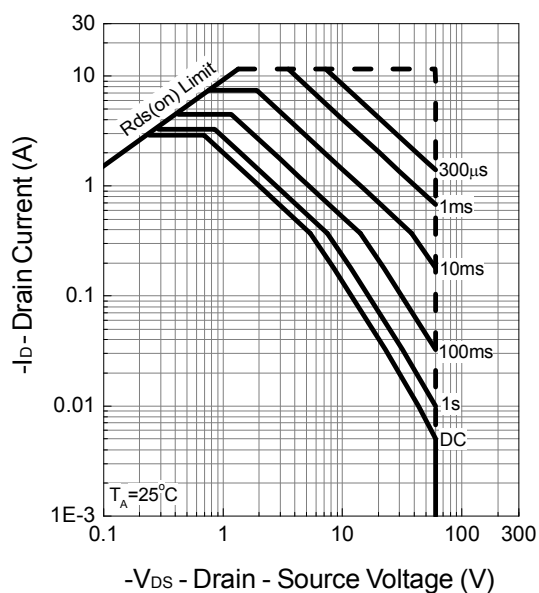
Power Dissipation



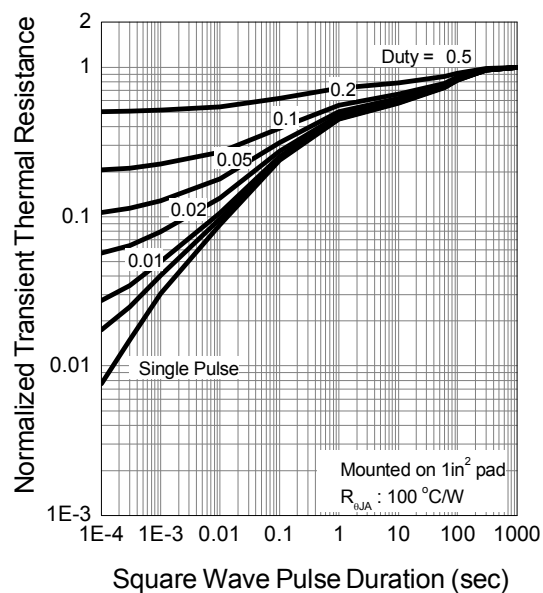
Drain Current



Safe Operation Area

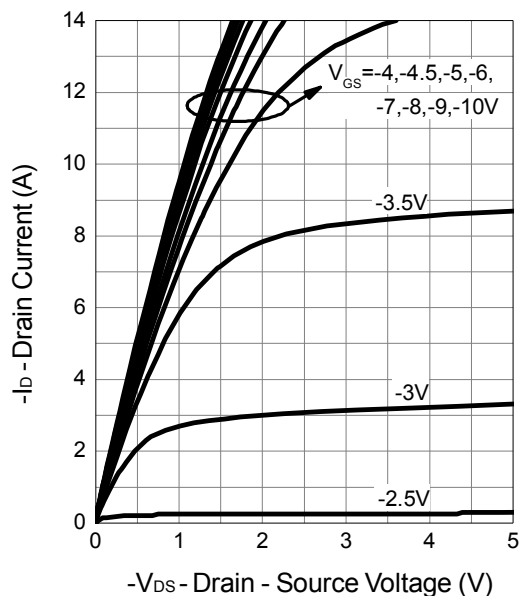


Thermal Transient Impedance

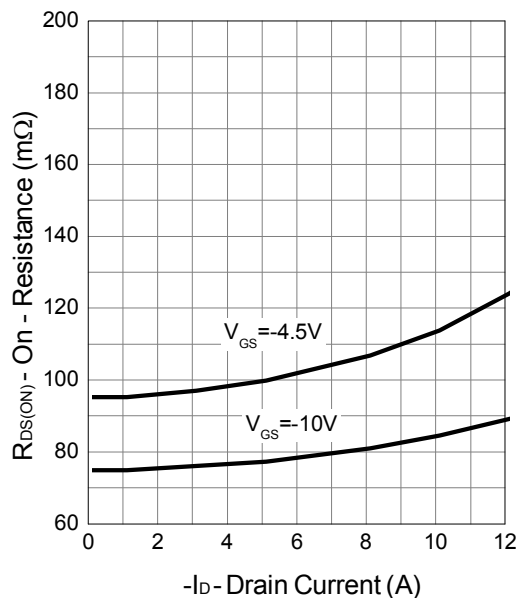


Typical Characteristics

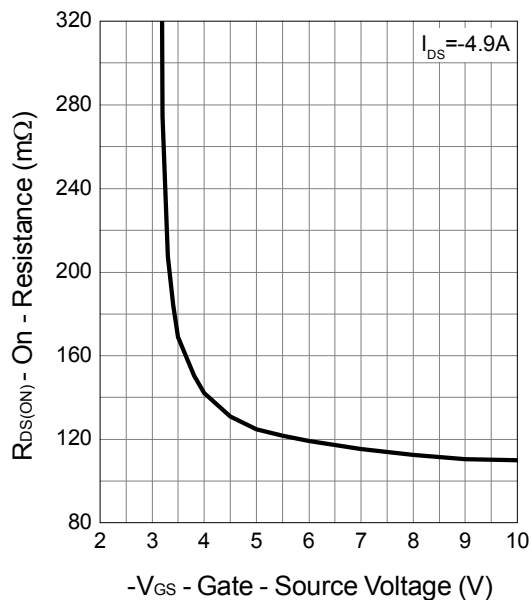
Output Characteristics



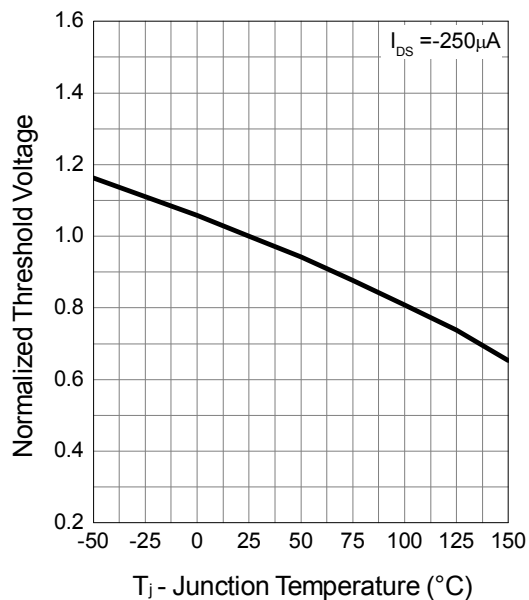
Drain-Source On Resistance



Gate-Source On Resistance

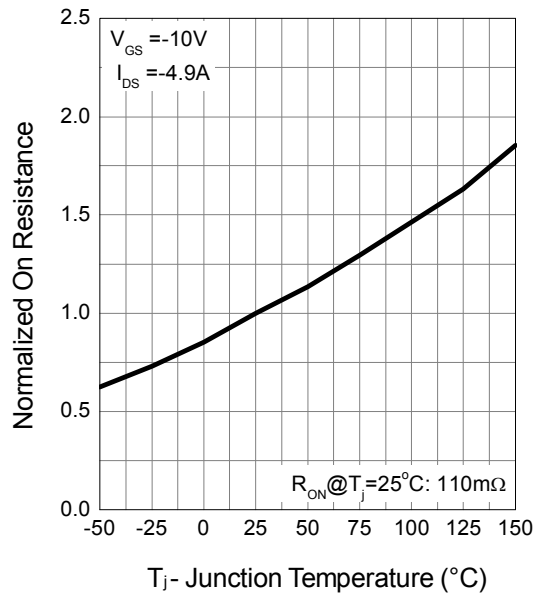


Gate Threshold Voltage

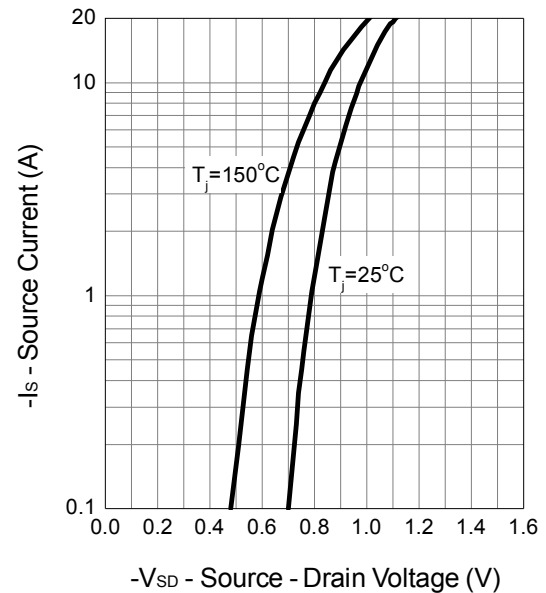


Typical Characteristics

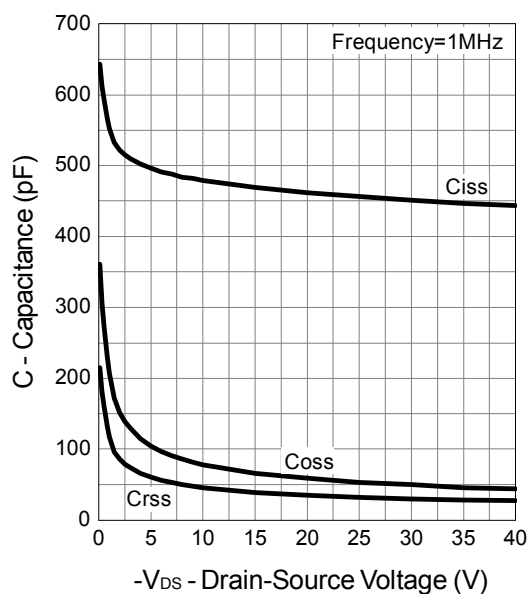
Drain-Source On Resistance



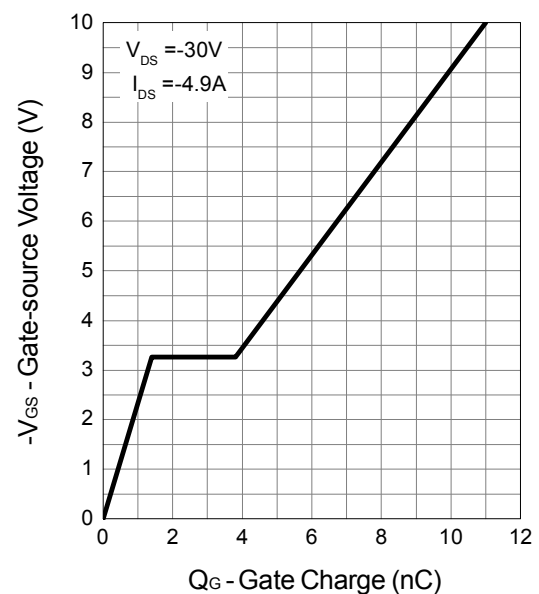
Source-Drain Diode Forward



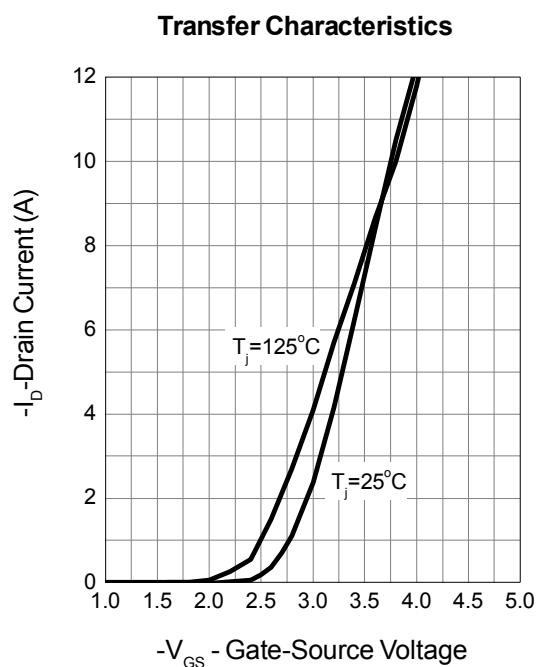
Capacitance



Gate Charge



Typical Characteristics



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